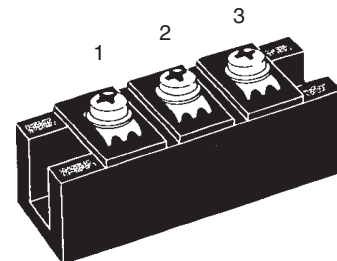
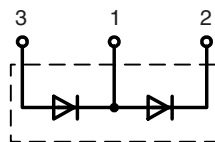


High Power Diode Modules

Preliminary data

$I_{FRMS} = 2x350 \text{ A}$
 $I_{FAVM} = 2x224 \text{ A}$
 $V_{RRM} = 1400-1800 \text{ V}$

V_{RSM} V V	V_{RRM} V V	Type
1500	1400	MDD 200-14N1
1700	1600	MDD 200-16N1
1900	1800	MDD 200-18N1



Symbol	Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	350	A
I_{FAVM}	$T_C = 100^\circ\text{C}; 180^\circ \text{ sine}$	224	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}; V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$	10500 A
		$t = 8.3 \text{ ms (60 Hz), sine}$	11200 A
I^2dt	$T_{VJ} = T_{VJM}; V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$	9100 A
		$t = 8.3 \text{ ms (60 Hz), sine}$	9700 A
I^2dt	$T_{VJ} = 45^\circ\text{C}; V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$	551000 A ² s
		$t = 8.3 \text{ ms (60 Hz), sine}$	527000 A ² s
I^2dt	$T_{VJ} = T_{VJM}; V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$	414000 A ² s
		$t = 8.3 \text{ ms (60 Hz), sine}$	395000 A ² s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$	3000 V~
		$t = 1 \text{ s}$	3600 V~
M_d	Mounting torque (M6)	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M6)	4.5-5.5/40-48	Nm/lb.in.
Weight	Typical including screws	120	g

Features

- International standard package
- Direct copper bonded Al_2O_3 -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~

Applications

- Supplies for DC power equipment
- DC supply for PWM inverter
- Field supply for DC motors
- Battery DC power supplies

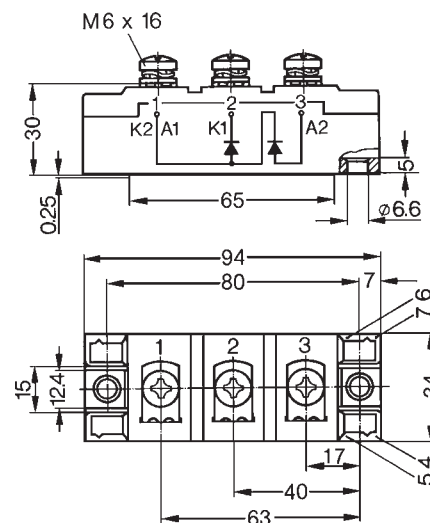
Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Conditions	Characteristic Values	
I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}$	20	mA
V_F	$I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.3	V
V_{T0}	For power-loss calculations only	0.8	V
r_T	$T_{VJ} = T_{VJM}$	1.5	mΩ
Q_S	$T_{VJ} = 125^\circ\text{C}; I_F = 300 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$	625	μC
		275	A
R_{thJC}	per diode; DC current	0.13	K/W
	per module	0.065	K/W
R_{thJK}	per diode; DC current	0.23	K/W
	per module	0.115	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions

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